TOSHIBA

TOSHIBA TRANSISTOR SILICON-GERMANIUM NPN EPITAXIAL PLANER TYPE

TENTATIVE

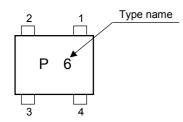
MT4S100T

UHF LOW NOISE AMPLIFIER APPLICATION

FEATURES

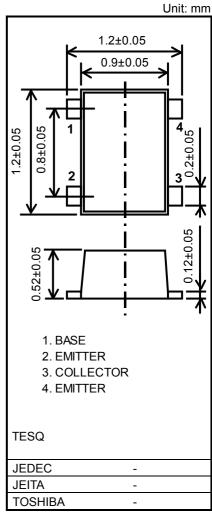
- Low Noise Figure :NF=0.72dB (@f=2GHz)
- High Gain:|S21e|²=17.0dB (@f=2GHz)

Marking



Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-Base voltage	V _{CBO}	6	V
Collector-Emitter voltage	V _{CEO}	3	V
Emitter-Base voltage	V _{EBO}	1.2	V
Collector-Current	Ι _C	15	mA
Base-Current	Ι _Β	7	mA
Collector Power dissipation	P _C	45	mW
Junction temperature	Тj	150	°C
Storage temperature Range	T _{stg}	-55~150	°C



Weight: 0.0015 g

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition Frequency	fT	V _{CE} =2V, I _C =10mA, f=2GHz	19	23	-	GHz
Insertion Gain	S21e ²	V _{CE} =2V, I _C =10mA, f=2GHz	14	17	-	dB
Noise Figure	NF	V _{CE} =2V, I _C =5mA, f=2GHz	-	0.72	1.0	dB

Electrical Characteristics (Ta = 25°C)

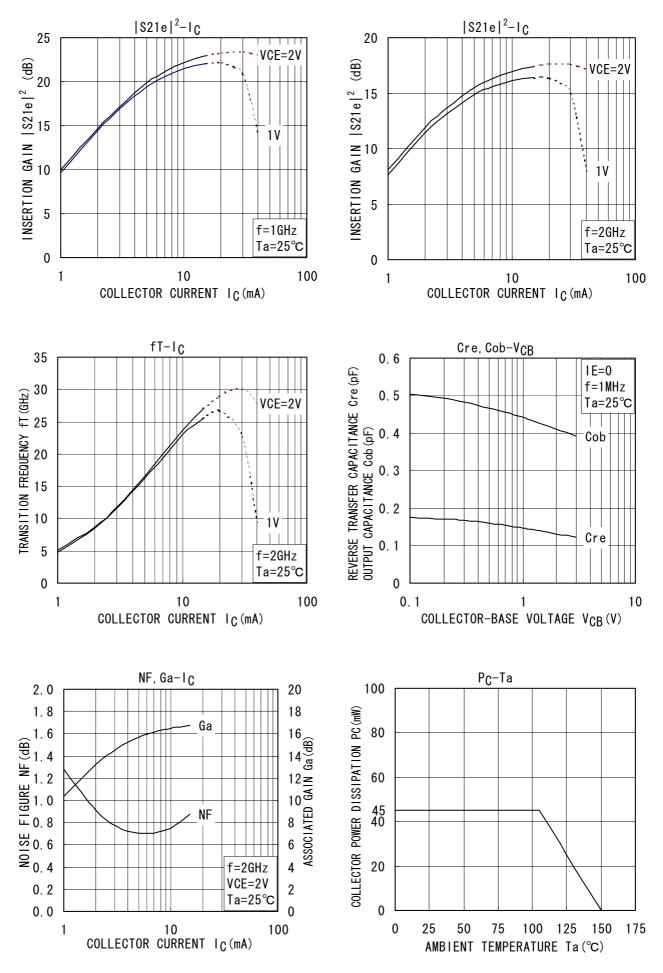
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} =6V, I _E =0	-	-	1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =1V, I _C =0	-	-	1	μA
DC Current Gain	hFE	V _{CE} =2V, I _C =10mA	200	-	400	-
Output Capacitance	C _{ob}	V _{CB} =2V, I _E =0, f=1MHz	-	0.41	0.6	pF
Reverse Transistor Capacitance	C _{re}	V _{CB} =2V, I _E =0, f=1MHz (Note 1)	-	0.14	0.2	pF

Note 1: Cre is measured by 3 terminal method with capacitance bridge.

Caution: This device is sensitive to electrostatic discharge.

Please make enough tool and equipment earthed when you handle.

TOSHIBA



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